

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	344	(257/64).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/25 16:08
L2	1931	(257/72).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/25 16:08
L3	204	(257/75).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/25 16:08
L4	1513	(257/66).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/08/25 16:09
LS	346	(poly adj Si polysilicon polycrystalline polycrystallization polycrystallizing recrystallized) near3 active and transistor and channel and grain adj (boundaries boundary) and display	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/25 16:09